IN THE CLAIMS

Please amend the claims as follows:

1. (Currently Amended) A pattern formation method comprising the steps of:

forming a resist film of a chemically amplified resist material including a base polymer~~,~~ and an acid generator for generating an acid through irradiation with light, the material further including sultone, carbohydrate sultone, sultine, or carbohydrate sultine; ~~and a material having negative polarity;~~

performing pattern exposure by selectively irradiating said resist film with exposing light while supplying an immersion solution onto said resist film; and

forming a resist pattern by developing said resist film after the pattern exposure.

2 – 3. (Canceled)

4. (Previously Presented) The pattern formation method of Claim 1,

wherein said immersion solution is water.

5. (Previously Presented) The pattern formation method of claim 1,

wherein said immersion solution is perfluoropolyether.

6. (Currently Amended) The pattern formation method of Claim 1,

wherein said exposing light is KrF excimer laser, ArF excimer laser, or F_2 laser~~, KrAr laser, or Ar_2 laser~~.

7. (Currently Amended) The pattern formation method of Claim ~~2~~ 1,

wherein said lactone is melavonic lactone, y-butyrolactone, y-valerolactone or ÿ-valerolactone.

8. (Currently Amended) The pattern formation method of Claim ~~2~~ 1,

wherein said polymer containing said lactone, said sultone, or said sultine is poly(acrylic ester) or poly(methacrylic ester).

9. (Currently Amended) The pattern formation method of Claim ~~2~~ 1,

wherein said carbohydrate lactone is D-gluconic acid δ–lactone, β-D-glucofurannurone acid y-lactone or L-mannal acid di-y-lactone.

10. (Currently Amended) The pattern formation method of claim ~~2~~ 1,

wherein said sultone is pentane-2, 5-sultone or naphthalene-1, 8-sultone.

11. (Currently Amended) The pattern formation method of Claim ~~2~~ 1,

wherein said sultine is 3H-2, 1-benzoxathiol=1-oxide.

12-21. (Canceled)